

IN THE CLAIMS

- 1 (Original). A method comprising:
forming a metal oxide dielectric using a liquid oxidizer.
- 2 (Original). The method of claim 1 including forming a metal oxide dielectric over a silicon substrate.
- 3 (Original). The method of claim 2 including forming the metal oxide dielectric of hafnium, zirconium, or tantalum.
- 4 (Original). The method of claim 1 wherein forming a metal oxide dielectric includes using physical vapor deposition to deposit metal atoms.
- 5 (Original). The method of claim 1 including using a liquid oxidizer selected from the group including solutions of O₃, H₂O₂ and organic peroxide.
- 6 (Original). The method of claim 1 wherein using a liquid oxidizer includes using an oxidizer in an aqueous solution.
- 7 (Original). A method comprising:
forming a dielectric using a metallic precursor; and
oxidizing said metallic precursor in a liquid.
- 8 (Original). The method of claim 7 including using a liquid oxidizer.
- 9 (Original). The method of claim 7 using an oxidizer in an aqueous solution.
- 10 (Original). The method of claim 7 including forming a metal oxide dielectric over a silicon substrate.

11 (Original). The method of claim 10 including forming a metal oxide dielectric of hafnium, zirconium, or tantalum.

12 (Original). The method of claim 7 including depositing a metallic film using physical vapor deposition.

13 (Original). The method of claim 7 including oxidizing using a liquid oxidizer selected from the group including solutions of O_3 , H_2O_2 , and organic peroxide.

14 (Original). A method comprising:
forming a dielectric using a metal precursor; and
oxidizing said metallic precursor in a liquid without forming an oxidized layer under the metallic precursor.

15 (Original). The method of claim 14 including using a liquid oxidizer.

16 (Original). The method of claim 14 using an oxidizer in an aqueous solution.

17 (Original). The method of claim 14 including forming a metal oxide dielectric over a silicon substrate.

18 (Original). The method of claim 17 including forming a metal oxide dielectric of hafnium, zirconium, or tantalum.

19 (Original). The method of claim 14 including depositing a metallic film using physical vapor deposition.

20 (Original). The method of claim 14 including oxidizing using a liquid oxidizer selected from the group including solutions of O_3 , H_2O_2 , and organic peroxide.

Claims 21-26 (Canceled).